

## Dual N-CHANNEL ENHANCEMENT MODE POWER MOSFET

# MTDN4228Q8

### Description

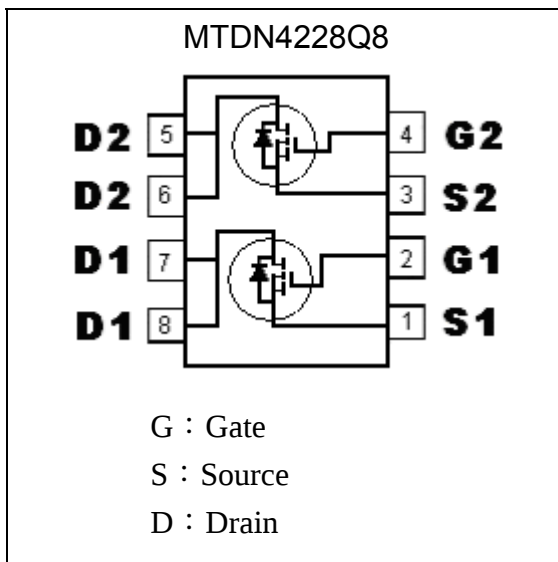
The MTDN4228Q8 provides the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness.

The SOP-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

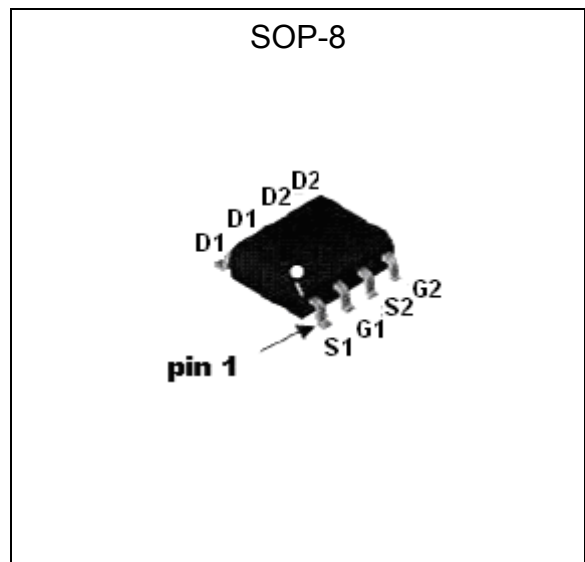
### Features

- $R_{DS(ON)} = 40m\Omega @ V_{GS} = 4.5V, I_D = 4A$
- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Dual N-ch MOSFET package
- Pb-free package

### Equivalent Circuit



### Outline



**Absolute Maximum Ratings** (Ta=25°C)

| Parameter                                   | Symbol | Limits   | Unit   |
|---------------------------------------------|--------|----------|--------|
| Drain-Source Breakdown Voltage              | BVDSS  | 30       | V      |
| Gate-Source Voltage                         | VGS    | ±20      | V      |
| Continuous Drain Current @TA=25 °C (Note 1) | ID     | 6.8      | A      |
| Continuous Drain Current @TA=70 °C (Note 1) | ID     | 5.5      | A      |
| Pulsed Drain Current (Note 2)               | IDM    | 40       | A      |
| Total Power Dissipation @ TA=25 °C          | Pd     | 2        | W      |
| Linear Derating Factor                      |        | 0.016    | W / °C |
| Operating Junction Temperature              | Tj     | -55~+150 | °C     |
| Storage Temperature                         | Tstg   | -55~+150 | °C     |
| Thermal Resistance, Junction-to-Ambient     | Rth,ja | 62.5     | °C/W   |

Note : 1.Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board, t≤10s.

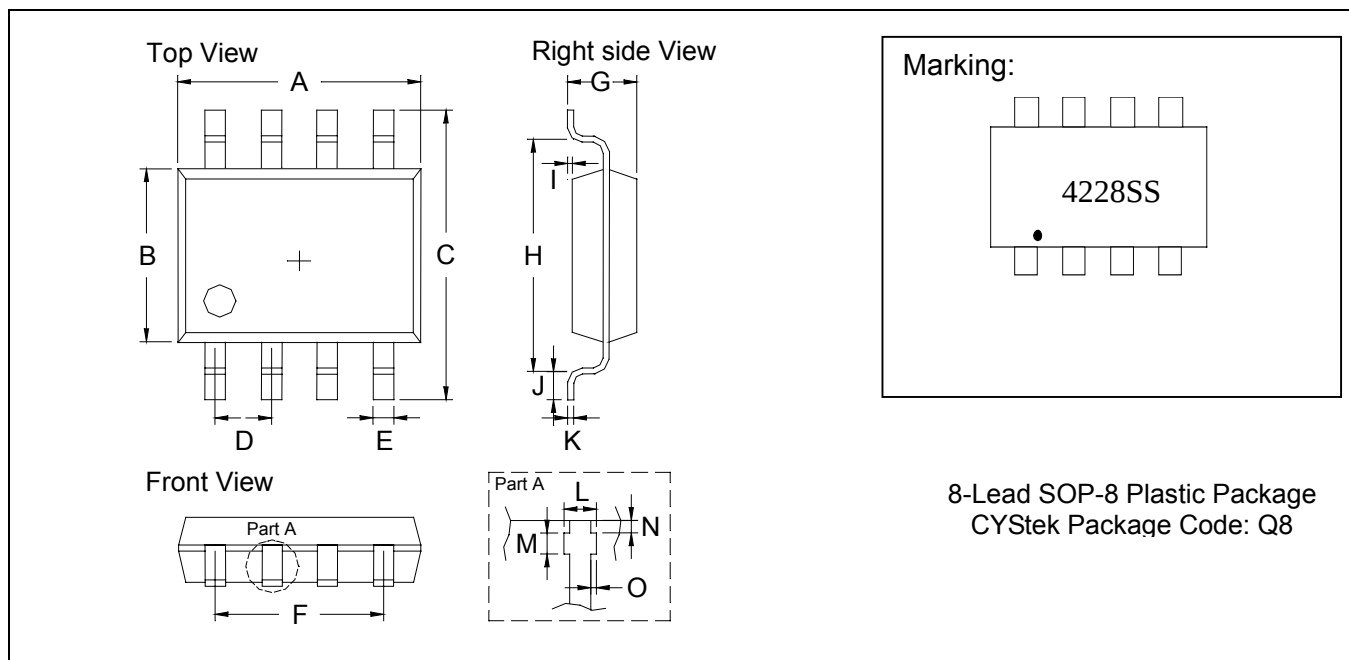
2.Pulse width limited by maximum junction temperature.

**Electrical Characteristics** (Ta=25°C)

| Symbol   | Min. | Typ. | Max. | Unit | Test Conditions                               |
|----------|------|------|------|------|-----------------------------------------------|
| BVDSS    | 30   | -    | -    | V    | VGS=0, ID=250μA                               |
| VGS(th)  | 1    | -    | 3    | V    | VDS=VGS, ID=-250μA                            |
| IGSS     | -    | -    | ±100 | nA   | VGS=±20V, VDS=0                               |
| IDSS     | -    | -    | 1    | μA   | VDS=30V, VGS=0                                |
| *RDS(ON) | -    | -    | 26   | mΩ   | ID=6A, VGS=10V                                |
|          | -    | -    | 40   |      | ID=4A, VGS=4.5V                               |
| *GFS     | -    | 15   | -    | S    | VDS=10V, ID=5A                                |
| Ciss     | -    | 580  | 930  | pF   | VDS=25V, VGS=0, f=1MHz                        |
| Coss     | -    | 150  | -    |      |                                               |
| Crss     | -    | 108  | -    |      |                                               |
| td(ON)   | -    | 10   | -    | ns   | VDD=15V, ID=1A,<br>VGS=10V, RGEN=3.3Ω, RD=15Ω |
| tr       | -    | 9    | -    | ns   |                                               |
| td(OFF)  | -    | 18   | -    | ns   |                                               |
| tf       | -    | 6    | -    | ns   |                                               |
| Qg       | -    | 9    | 15   | nC   | VDS=24V, ID=6.8A,<br>VGS=4.5V,                |
| Qgs      | -    | 2    | -    | nC   |                                               |
| Qgd      | -    | 6    | -    | nC   |                                               |
| *VSD     | -    | -    | 1.3  | V    | VGS=0V, ISD=1.7A                              |

\*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

## SOP-8 Dimension



\*: Typical

| DIM | Inches |        | Millimeters |      | DIM | Inches |        | Millimeters |      |
|-----|--------|--------|-------------|------|-----|--------|--------|-------------|------|
|     | Min.   | Max.   | Min.        | Max. |     | Min.   | Max.   | Min.        | Max. |
| A   | 0.1909 | 0.2007 | 4.85        | 5.10 | I   | 0.0019 | 0.0078 | 0.05        | 0.20 |
| B   | 0.1515 | 0.1555 | 3.85        | 3.95 | J   | 0.0118 | 0.0275 | 0.30        | 0.70 |
| C   | 0.2283 | 0.2441 | 5.80        | 6.20 | K   | 0.0074 | 0.0098 | 0.19        | 0.25 |
| D   | 0.0480 | 0.0519 | 1.22        | 1.32 | L   | 0.0145 | 0.0204 | 0.37        | 0.52 |
| E   | 0.0145 | 0.0185 | 0.37        | 0.47 | M   | 0.0118 | 0.0197 | 0.30        | 0.50 |
| F   | 0.1472 | 0.1527 | 3.74        | 3.88 | N   | 0.0031 | 0.0051 | 0.08        | 0.13 |
| G   | 0.0570 | 0.0649 | 1.45        | 1.65 | O   | 0.0000 | 0.0059 | 0.00        | 0.15 |
| H   | 0.1889 | 0.2007 | 4.80        | 5.10 |     |        |        |             |      |

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

### Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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